

# P3CD10170B

1700V/10A SiC Power Schottky Barrier Diode Product



**POWERCUBESEMI, INC.**

Potential · Convergence · Smart

## Features

- Positive temperature coefficient for easy parallel use
- Switching characteristics that are not affected by temperature
- Maximum operating temperature 175 °C
- Zero reverse recovery current
- Zero forward recovery voltage

## Benefits

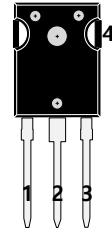
- Unipolar device
- Greatly reduce switching losses
- No thermal crash in parallel devices
- Reduce system dependence on heat sinks

## Applications

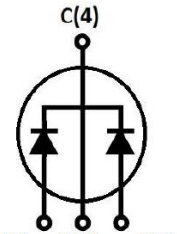
- Switch Mode Power Supply (SMPS), Power Factor Correction (PFC)
- Motor drive, photovoltaic inverter, uninterruptible power supply, Wind turbines, train traction systems, electric vehicles.

Key Characteristics		
$V_{RRM}$	1700	V
$I_F, T_C \leq 160^\circ\text{C}$	5*	A
$Q_C$	65*	nC

\* : per Leg



PKG : TO-247



A(1) C(2) A(3)



## Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Test Condition	Value	Unit
$V_{RRM}$	Repetitive Peak Reverse Voltage		1700	V
$V_{RSM}$	Surge Peak Reverse Voltage		1700	V
$V_{DC}$	DC Blocking Voltage		1700	V
$I_F$	Continuous Forward Current	$T_C=25^\circ\text{C}$	24*	A
		$T_C=135^\circ\text{C}$	12*	A
		$T_C=160^\circ\text{C}$	5*	A
$I_{FRM}$	Repetitive Peak Forward Surge Current	$T_C=25^\circ\text{C}$ , $t_p=10\text{ms}$ , Half Sine Wave, $D=0.3$	25*	A
$I_{FSM}$	Non-repetitive Peak Forward Surge Current	$T_C=25^\circ\text{C}$ , $t_p=10\text{ms}$ , Half Sine Wave	120*	A
$P_{TOT}$	Power Dissipation	$T_C=25^\circ\text{C}$	142*	W
		$T_C=110^\circ\text{C}$	61*	
$T_j$	Operating Junction		-55 to 175	$^\circ\text{C}$
$T_{stg}$	Storage Temperature		-55 to 175	$^\circ\text{C}$



**Thermal Characteristics**

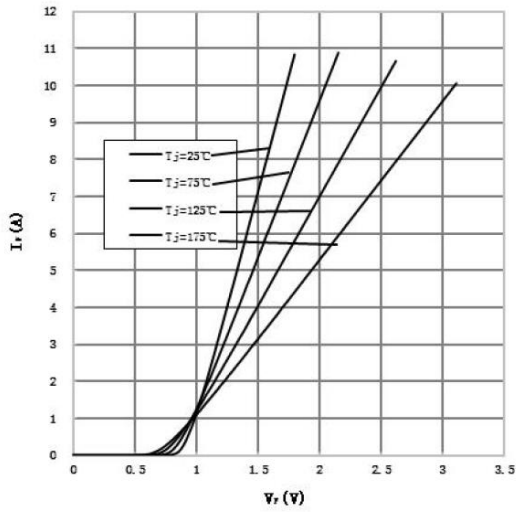
Symbol	Parameter	Test Condition	Value	Unit
			Typ.	
$R_{thJc}$	Thermal resistance from junction to case		1.06* 0.53**	°C/W

**Electrical Characteristics, Nomination temperature Tj=25°C**

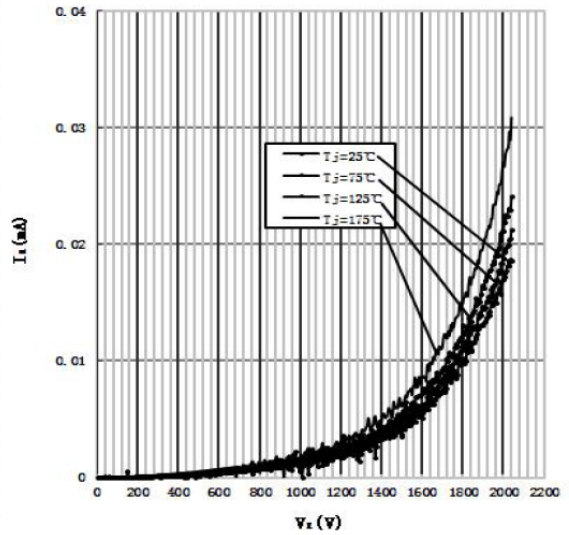
Symbol	Parameter	Test Condition	Numerical		Unit
			Typ.	Max.	
$V_F$	Forward Voltage	$I_F=5A, T_j=25^\circ C$	1.4	1.7	V
		$I_F=5A, T_j=175^\circ C$	2	2.5	
$I_R$	Reverse Current	$V_R=1700V, T_j=25^\circ C$	10	50	$\mu A$
		$V_R=1700V, T_j=175^\circ C$	20	100	
$Q_C$	Total capacitive Charge	$V_R=1200V, T_j=150^\circ C$ $Q_C = \int_0^{V_R} C(V)dV$	65	-	nC
C	Total Capacitance	$V_R=0V, T_j=25^\circ C, f=1MHZ$	780	800	pF
		$V_R=400V, T_j=25^\circ C, f=1MHZ$	48	50	
		$V_R=800V, T_j=25^\circ C, f=1MHZ$	34.5	35	

## Performance Graphs

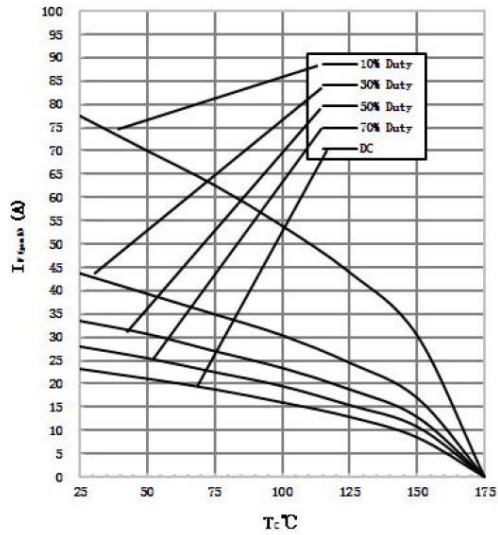
1) Forward IV characteristics as a function of  $T_j$



2) Reverse IV characteristics as a function of  $T_j$



3) Current Derating



4) Capacitance VS. reverse voltage

